Supplementary Information (SI) for Physical Chemistry Chemical Physics.

Polarization-resolved Raman resonant excitation of surface and bulk electronic bands and phonons in MBE grown topological insulator thin films

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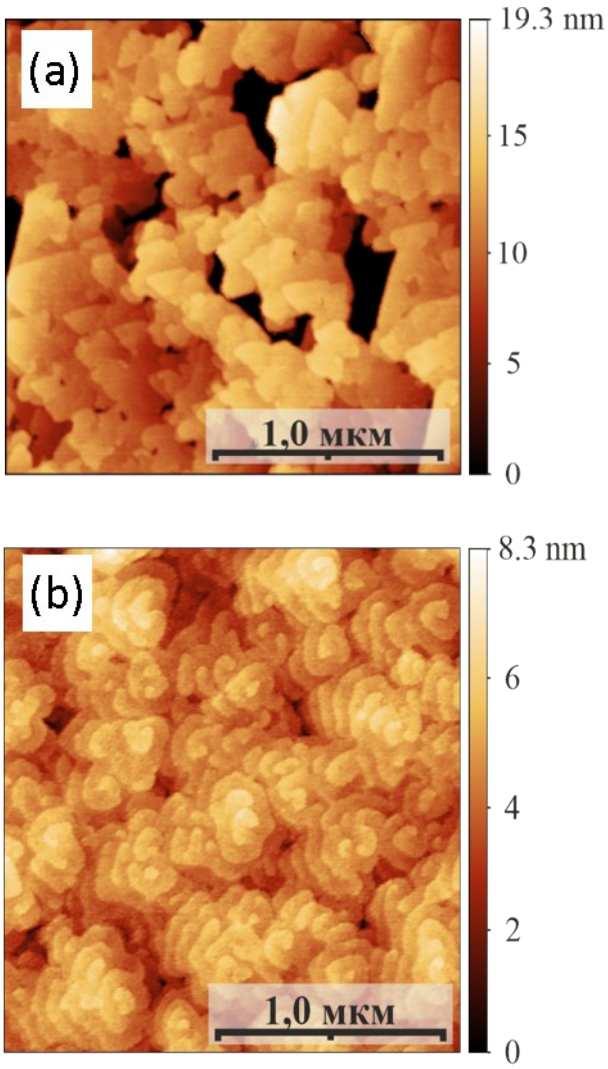

Fig. SI-1. Topography of (a) Bi2Te3 and (b) BSTS films

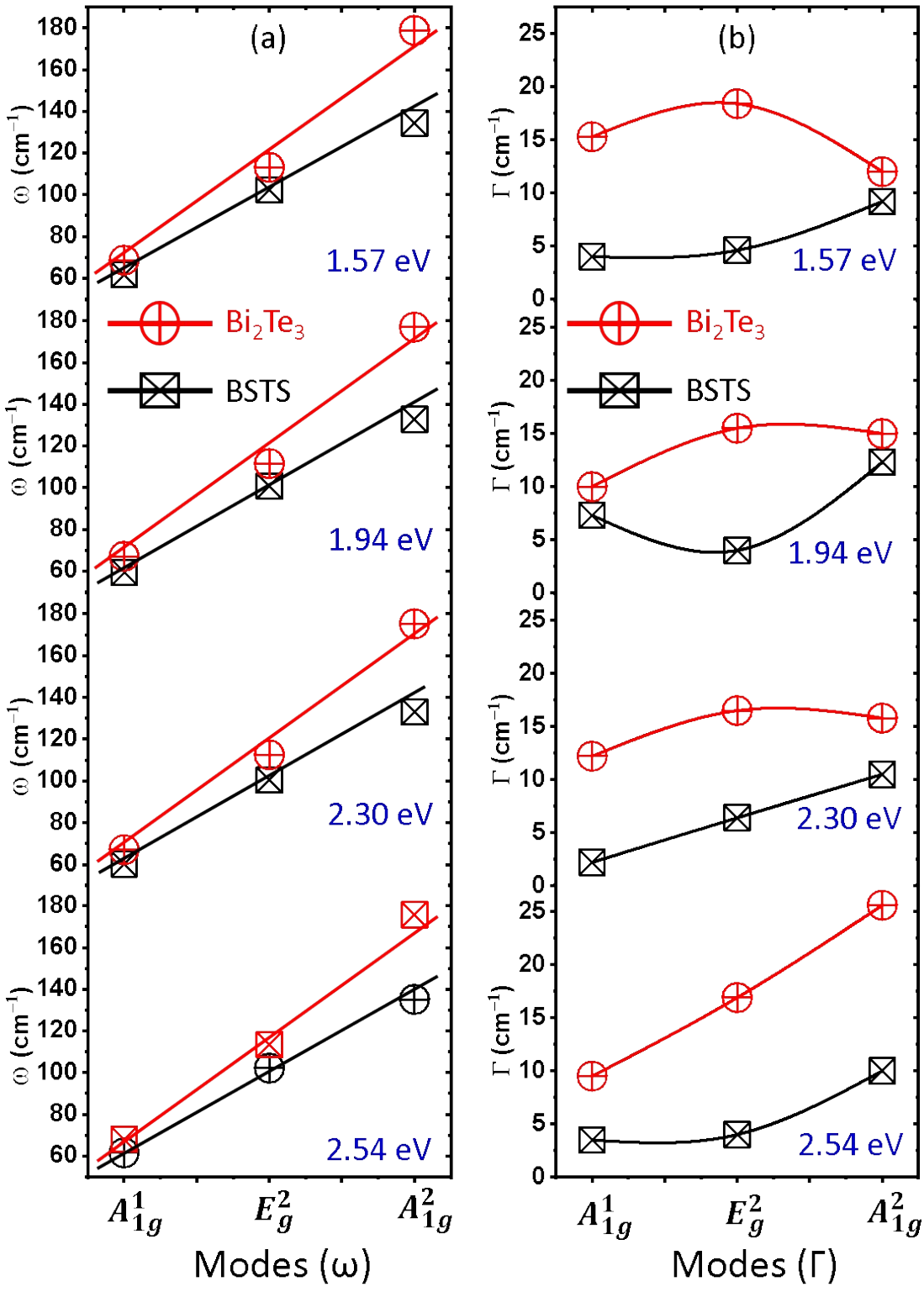

Fig. SI-2. Frequency shift of A_{1g}^{1}, E_g^2 and A_{1g}^{2} modes for Bi_2Te_3 and BSTS film (a) and mode width (b) at four different excitation energy of photon E_p 1.57, 1.94, 2.3 and 2.94 eV.